

# Jan Kuzmik

## List of Publications by Year in descending order

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152  
papers

3,311  
citations

159525

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161767

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155  
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155  
docs citations

155  
times ranked

2229  
citing authors

#	ARTICLE	IF	CITATIONS
1	Analysis and Modeling of Vertical Current Conduction and Breakdown Mechanisms in Semi-Insulating GaN Grown on GaN: Role of Deep Levels. IEEE Transactions on Electron Devices, 2021, 68, 2365-2371.	1.6	5
2	InN crystal habit, structural, electrical, and optical properties affected by sapphire substrate nitridation in N-polar InN/InAlN heterostructures. Semiconductor Science and Technology, 2021, 36, 075025.	1.0	0
3	Invited: Polarization engineering in GaN-based normally-off transistors. , 2021, , .		0
4	InN: Breaking the limits of solid-state electronics. AIP Advances, 2021, 11, .	0.6	7
5	Growth evolution of N-polar indium-rich InAlN layer on c-sapphire via strain relaxation by ultrathin AlON interlayer. Applied Surface Science, 2020, 502, 144086.	3.1	8
6	Correlation of Threading Dislocations with the Electron Concentration and Mobility in InN Heteroepitaxial Layers Grown by MBE. ECS Journal of Solid State Science and Technology, 2020, 9, 015006.	0.9	14
7	A systematic study of MOCVD reactor conditions and Ga memory effect on properties of thick InAl(GaN) layers: a complete depth-resolved investigation. CrystEngComm, 2020, 22, 130-141.	1.3	2
8	Growth and Properties of N-Polar InN/InAlN Heterostructures. Physica Status Solidi (A) Applications and Materials Science, 2020, 217, 2000197.	0.8	4
9	Investigation of interfaces and threshold voltage instabilities in normally-off MOS-gated InGaN/AlGaIn/GaN HEMTs. Applied Surface Science, 2020, 528, 146824.	3.1	3
10	Semi-insulating GaN for vertical structures: role of substrate selection and growth pressure. Materials Science in Semiconductor Processing, 2020, 118, 105203.	1.9	7
11	Morphology, Crystalline Quality, and Optical Properties of MOCVD-grown InN/InAlN Heterostructures. , 2020, , .		1
12	Device and Circuit Models of Monolithic InAlN/GaN NAND and NOR Logic Cells Comprising D- and E-Mode HEMTs. Journal of Circuits, Systems and Computers, 2019, 28, 1940009.	1.0	1
13	Bandgap, electrical and structural properties of thick InN (0001) films grown under optimal conditions. Journal of Physics: Conference Series, 2019, 1190, 012010.	0.3	1
14	InGaIn/(GaN)/AlGaIn/GaN normally-off metal-oxide-semiconductor high-electron mobility transistors with etched access region. Japanese Journal of Applied Physics, 2019, 58, SCCD21.	0.8	3
15	Evidence of relationship between strain and In-incorporation: Growth of N-polar In-rich InAlN buffer layer by OMCVD. Journal of Applied Physics, 2019, 125, .	1.1	10
16	Impact of oxide/barrier charge on threshold voltage instabilities in AlGaIn/GaN metal-oxide-semiconductor heterostructures. Materials Science in Semiconductor Processing, 2019, 91, 356-361.	1.9	4
17	Structural, electrical, and optical properties of annealed InN films grown on sapphire and silicon substrates. Thin Solid Films, 2019, 672, 114-119.	0.8	6
18	Effect of temperature and carrier gas on the properties of thick $I_n$ $n$ $x$ $A$ $I_n$ $m$ $r$ $o$	3.1	9

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19	Generation of hole gas in non-inverted InAl(Ga)N/GaN heterostructures. Applied Physics Express, 2019, 12, 014001.	1.1	5
20	Characterization of Monolithic InAlN/GaN NAND Logic Cell Supported by Circuit and Device Simulations. IEEE Transactions on Electron Devices, 2018, 65, 2666-2669.	1.6	7
21	State of the art on gate insulation and surface passivation for GaN-based power HEMTs. Materials Science in Semiconductor Processing, 2018, 78, 85-95.	1.9	108
22	Determination of Secondary-Ions Yield in SIMS Depth Profiling of Si, Mg, and C Ions Implanted GaN Epitaxial Layers. , 2018, , .		2
23	Creation of Two-Dimensional Electron Gas and Role of Surface Donors in III-N Metal-Oxide-Semiconductor High-Electron Mobility Transistors. Physica Status Solidi (A) Applications and Materials Science, 2018, 215, 1800090.	0.8	5
24	Enhancement of channel electric field in AlGaIn/GaN multi-nanochannel high electron mobility transistors. Journal of Applied Physics, 2018, 124, 224502.	1.1	5
25	Simulation Analysis of InAlN/GaN Monolithic NAND Logic Cell. , 2018, , .		1
26	Characterization of interface states in AlGaIn/GaN metal-oxide-semiconductor heterostructure field-effect transistors with HfO <sub>2</sub> gate dielectric grown by atomic layer deposition. Applied Surface Science, 2018, 461, 255-259.	3.1	11
27	Device and circuit models of InAlN/GaN D- and dual-gate E-mode HEMTs for design and characterisation of monolithic NAND logic cell. , 2018, , .		3
28	Non-conventional scans in high-resolution X-ray diffraction analysis of epitaxial systems. Applied Surface Science, 2018, 461, 23-32.	3.1	5
29	Technology and performance of E/D-mode InAlN/GaN HEMTs for mixed-signal electronics. , 2018, , .		0
30	Low-temperature atomic layer deposition-grown Al <sub>2</sub> O <sub>3</sub> gate dielectric for GaN/AlGaIn/GaN MOS HEMTs: Impact of deposition conditions on interface state density. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2017, 35, .	0.6	21
31	Polarization-Engineered n <sup>+</sup> GaN/InGaIn/AlGaIn/GaN Normally-Off MOS HEMTs. Physica Status Solidi (A) Applications and Materials Science, 2017, 214, 1700407.	0.8	6
32	Annealing, temperature, and bias-induced threshold voltage instabilities in integrated E/D-mode InAlN/GaN MOS HEMTs. Applied Physics Letters, 2017, 111, .	1.5	10
33	Investigation of "surface donors"™ in Al <sub>2</sub> O <sub>3</sub> /AlGaIn/GaN metal-oxide-semiconductor heterostructures: Correlation of electrical, structural, and chemical properties. Applied Surface Science, 2017, 426, 656-661.	3.1	27
34	High resolution physical analysis of ohmic contact formation at GaN-HEMT devices. Microelectronics Reliability, 2017, 76-77, 338-343.	0.9	6
35	Current conduction mechanism and electrical break-down in InN grown on GaN. Applied Physics Letters, 2017, 110, .	1.5	8
36	Performance analysis of monolithically integrated depletion-/enhancement-mode InAlN/GaN heterostructure HEMT transistors. , 2017, , .		0

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37	Characterization of capture cross sections of interface states in dielectric/III-nitride heterojunction structures. Journal of Applied Physics, 2016, 119, .	1.1	21
38	Post-deposition annealing and thermal stability of integrated self-aligned E/D-mode n <sup>++</sup> GaN/InAlN/AlN/GaN MOS HEMTs. , 2016, , .		2
39	Temperature-dependent of sub-threshold slope of AlGaIn/GaN MOSHFETs with HfO <sub>2</sub> gate oxide prepared by ALD. , 2016, , .		0
40	Effect of HCl pretreatment on the oxide/semiconductor interface state density in AlGaIn/GaN MOS-HEMT structures with MOCVD grown Al <sub>2</sub> O <sub>3</sub> gate dielectric. , 2016, , .		0
41	DC and pulsed IV characterisation of AlGaIn/GaN MOS-HEMT structures with Al <sub>2</sub> O <sub>3</sub> gate dielectric prepared by various techniques. , 2016, , .		0
42	Technology of integrated self-aligned E/D-mode n <sup>++</sup> GaN/InAlN/AlN/GaN MOS HEMTs for mixed-signal electronics. Semiconductor Science and Technology, 2016, 31, 065011.	1.0	12
43	Gate Reliability Investigation in Normally-Off p-Type-GaN Cap/AlGaIn/GaN HEMTs Under Forward Bias Stress. IEEE Electron Device Letters, 2016, 37, 385-388.	2.2	126
44	Investigation of gate-diode degradation in normally-off p-GaN/AlGaIn/GaN high-electron-mobility transistors. Applied Physics Letters, 2015, 107, .	1.5	46
45	Elimination of surface band bending on N-polar InN with thin GaN capping. Applied Physics Letters, 2015, 107, .	1.5	7
46	Self-aligned normally-off metal-oxide-semiconductor n <sup>++</sup> GaN/InAlN/GaN high electron mobility transistors. Physica Status Solidi (A) Applications and Materials Science, 2015, 212, 1086-1090.	0.8	23
47	Impact of the buffer structure on trapping characteristics of normally-off p-GaN/AlGaIn/GaN HEMTs for power switching applications. , 2014, , .		0
48	Different polarities of InN (0001) heterostructures on Si (111) substrates. , 2014, , .		0
49	Time resolved EBIC study of InAlN/GaN HFETs. , 2014, , .		0
50	Material and electrical properties of N-polar (GaN)/InN surfaces. , 2014, , .		0
51	Adjustment of threshold voltage in AlN/AlGaIn/GaN high-electron mobility transistors by plasma oxidation and Al <sub>2</sub> O <sub>3</sub> atomic layer deposition overgrowth. Applied Physics Letters, 2014, 104, .	1.5	31
52	Proposal of normally-off InN-channel high-electron mobility transistors. Semiconductor Science and Technology, 2014, 29, 035015.	1.0	11
53	Impact of GaN cap on charges in Al <sub>2</sub> O <sub>3</sub> /(GaN)/AlGaIn/GaN metal-oxide-semiconductor heterostructures analyzed by means of capacitance measurements and simulations. Journal of Applied Physics, 2014, 116, .	1.1	43
54	Degradation of AlGaIn/GaN high-electron mobility transistors in the current-controlled off-state breakdown. Journal of Applied Physics, 2014, 115, 164504.	1.1	0

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55	Hot-Electron-Related Degradation in InAlN/GaN High-Electron-Mobility Transistors. IEEE Transactions on Electron Devices, 2014, 61, 2793-2801.	1.6	37
56	Simulation study of interface traps and bulk traps in n++GaN/InAlN/AlN/GaN high electron mobility transistors. Applied Surface Science, 2014, 312, 157-161.	3.1	14
57	Self-Heating in GaN Transistors Designed for High-Power Operation. IEEE Transactions on Electron Devices, 2014, 61, 3429-3434.	1.6	40
58	Ni/Au/Al <sub>2</sub> O <sub>3</sub> gate stack prepared by low-temperature ALD and lift-off for MOS HEMTs. Microelectronic Engineering, 2013, 112, 204-207.	1.1	10
59	Schottky-barrier normally off GaN/InAlN/AlN/GaN HEMT with selectively etched access region. IEEE Electron Device Letters, 2013, 34, 432-434.	2.2	33
60	Control of Threshold Voltage in GaN Based Metal-Oxide-Semiconductor High-Electron Mobility Transistors towards the Normally-Off Operation. Japanese Journal of Applied Physics, 2013, 52, 08JN08.	0.8	26
61	A Promising New n++-GaN/InAlN/GaN HEMT Concept for High-Frequency Applications. ECS Transactions, 2013, 50, 291-296.	0.3	4
62	Degradation Study of Single and Double-Heterojunction InAlN/GaN HEMTs by Two-Dimensional Simulation. ECS Transactions, 2013, 50, 223-228.	0.3	2
63	Bulk and interface trapping in the gate dielectric of GaN based metal-oxide-semiconductor high-electron-mobility transistors. Applied Physics Letters, 2013, 102, .	1.5	51
64	N-Polarity InN/GaN/InAlN High-Electron-Mobility Transistors. Applied Physics Express, 2012, 5, 044101.	1.1	17
65	Buffer-Related Degradation Aspects of Single and Double-Heterostructure Quantum Well InAlN/GaN High-Electron-Mobility Transistors. Japanese Journal of Applied Physics, 2012, 51, 054102.	0.8	2
66	Electrothermal analysis of In<math>0.12</math>/Al<math>0.88</math>/N/GaN HEMTs. , 2012, , .		0
67	Early stage degradation of InAlN/GaN HEMTs during electrical stress. , 2012, , .		1
68	A comprehensive analytical model for threshold voltage calculation in GaN based metal-oxide-semiconductor high-electron-mobility transistors. Applied Physics Letters, 2012, 100, .	1.5	130
69	Material and device issues of InAlN/GaN heterostructures. , 2012, , .		4
70	Influence of processing and annealing steps on electrical properties of InAlN/GaN high electron mobility transistor with Al <sub>2</sub> O <sub>3</sub> gate insulation and passivation. Solid-State Electronics, 2012, 67, 74-78.	0.8	17
71	Buffer-Related Degradation Aspects of Single and Double-Heterostructure Quantum Well InAlN/GaN High-Electron-Mobility Transistors. Japanese Journal of Applied Physics, 2012, 51, 054102.	0.8	13
72	Electrical properties of InAlN/GaN high electron mobility transistor with Al <sub>2</sub> O <sub>3</sub> , ZrO <sub>2</sub> , and GdScO <sub>3</sub> gate dielectrics. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2011, 29, .	0.6	30

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73	Normally-off InAlN/GaN HEMTs with n <sup>+</sup> GaN cap layer: A simulation study. , 2011, , .		1
74	Thermal characterization of MBE-grown GaN/AlGaIn/GaN device on single crystalline diamond. Journal of Applied Physics, 2011, 109, .	1.1	25
75	Improvements of High Performance 2-nm-thin InAlN/AlN Barrier Devices by Interface Engineering. , 2011, , .		0
76	Proposal of High-Electron Mobility Transistors With Strained InN Channel. IEEE Transactions on Electron Devices, 2011, 58, 720-724.	1.6	33
77	Proposal and Performance Analysis of Normally Off $n^+$ GaN/InAlN/AlN/GaN HEMTs With 1-nm-Thick InAlN Barrier. IEEE Transactions on Electron Devices, 2010, 57, 2144-2154.	1.6	31
78	Optimization of the ohmic contact processing in InAlN//GaN high electron mobility transistors for lower temperature of annealing. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 108-111.	0.8	6
79	Study of Si implantation into Mg-doped GaN for MOSFETs. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 1964-1966.	0.8	3
80	Current transport and barrier height evaluation in Ni/InAlN/GaN Schottky diodes. Applied Physics Letters, 2010, 96, 223501.	1.5	32
81	Metal-related gate sinking due to interfacial oxygen layer in Ir/InAlN high electron mobility transistors. Applied Physics Letters, 2010, 96, 263515.	1.5	11
82	Characterization of Plasma-Induced Damage of Selectively Recessed GaN/InAlN/AlN/GaN Heterostructures Using SiCl <sub>4</sub> and SF <sub>6</sub> . Japanese Journal of Applied Physics, 2010, 49, 116506.	0.8	11
83	Role of the gate-to-drain distance in the performance of the normally-off InAlN/GaN HEMTs. , 2010, , .		0
84	InAlN/GaN metal-oxide-semiconductor high electron mobility transistor with Al <sub>2</sub> O <sub>3</sub> insulating films grown by metal organic chemical vapor deposition using Ar and NH <sub>3</sub> carrier gases. Journal of Vacuum Science & Technology B, 2009, 27, 218.	1.3	10
85	Interface States and Trapping Effects in Al <sub>2</sub> O <sub>3</sub> - and ZrO <sub>2</sub> /InAlN/AlN/GaN Metal-Oxide Semiconductor Heterostructures. Japanese Journal of Applied Physics, 2009, 48, 090201.	0.8	14
86	Self-heating phenomena in high-power III-N transistors and new thermal characterization methods developed within EU project TARGET. International Journal of Microwave and Wireless Technologies, 2009, 1, 153-160.	1.5	10
87	Atomic Layer Deposition of High-k Oxides on InAlN/GaN-based Materials. ECS Transactions, 2009, 25, 123-129.	0.3	0
88	Off-state breakdown in InAlN/AlN/GaN high electron mobility transistors. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S925.	0.8	16
89	Low resistance ohmic contacts annealed at 600 °C on a InAlN/GaN heterostructure with SiCl <sub>4</sub> -reactive ion etching surface treatment. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S999-S1002.	0.8	13
90	Thermally induced voltage shift in capacitance-voltage characteristics and its relation to oxide/semiconductor interface states in Ni/Al <sub>2</sub> O <sub>3</sub> /InAlN/GaN heterostructures. Semiconductor Science and Technology, 2009, 24, 035008.	1.0	39

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91	Ultrathin InAlN/AlN Barrier HEMT With High Performance in Normally Off Operation. IEEE Electron Device Letters, 2009, 30, 1030-1032.	2.2	57
92	Current collapse reduction in InAlN/GaN MOS HEMTs by in situ surface pre-treatment and atomic layer deposition of ZrO <sub>2</sub> high-k gate dielectrics. Electronics Letters, 2009, 45, 570.	0.5	17
93	Analysis of degradation mechanisms in lattice-matched InAlN/GaN high-electron-mobility transistors. Journal of Applied Physics, 2009, 106, .	1.1	96
94	InAlN/GaN heterostructures for microwave power and beyond. , 2009, , .		4
95	Influence of GaN capping on performance of InAlN/AlN/GaN MOS HEMT with Al <sub>2</sub> O <sub>3</sub> gate insulation grown by CVD. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 1956-1958.	0.8	10
96	Technology and Performance of InAlN/AlN/GaN HEMTs With Gate Insulation and Current Collapse Suppression Using ZrO <sub>2</sub> or HfO <sub>2</sub> . IEEE Transactions on Electron Devices, 2008, 55, 937-941.	1.6	86
97	InAlN/GaN MOSHEMT with Al <sub>2</sub> O <sub>3</sub> insulating film. , 2008, , .		0
98	MOCVD of HfO <sub>2</sub> and ZrO <sub>2</sub> high-k gate dielectrics for InAlN/AlN/GaN MOS-HEMTs. Semiconductor Science and Technology, 2007, 22, 1272-1275.	1.0	62
99	Current gain collapse in HBTs analysed by transient interferometric mapping method. , 2007, , .		1
100	Gate insulation and drain current saturation mechanism in InAlN-GaN metal-oxide-semiconductor high-electron-mobility transistors. Applied Physics Letters, 2007, 91, .	1.5	71
101	Investigation of the thermal boundary resistance at the III-Nitride/substrate interface using optical methods. Journal of Applied Physics, 2007, 101, 054508.	1.1	55
102	Optimization and performance of Al <sub>2</sub> O <sub>3</sub> /GaN metal-oxide-semiconductor structures. Microelectronics Reliability, 2007, 47, 790-793.	0.9	15
103	Gate-lag and drain-lag effects in (GaN)/InAlN/GaN and InAlN/AlN/GaN HEMTs. Physica Status Solidi (A) Applications and Materials Science, 2007, 204, 2019-2022.	0.8	49
104	Transient self-heating effects in multifinger AlGaN/GaN HEMTs with metal airbridges. Solid-State Electronics, 2007, 51, 969-974.	0.8	11
105	Experimental Investigation on Carrier Dynamics at the Thermal Breakdown. AIP Conference Proceedings, 2007, , .	0.3	0
106	Rapid thermal annealing and performance of Al <sub>2</sub> O <sub>3</sub> /GaN metal-oxide-semiconductor structures. , 2006, , .		0
107	InAlN/GaN HEMTs: a first insight into technological optimization. IEEE Transactions on Electron Devices, 2006, 53, 422-426.	1.6	176
108	Current conduction and saturation mechanism in AlGaN-GaN ungated structures. Journal of Applied Physics, 2006, 99, 123720.	1.1	22

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109	Temperature analysis of AlGaIn/GaN High-Electron-Mobility Transistors using micro-Raman scattering spectroscopy and Transient Interferometric Mapping. , 2006, , .		5
110	Temperature dependence of GaN Schottky diodes Iâ€V characteristics. Microelectronic Engineering, 2005, 81, 181-187.	1.1	47
111	Transient Thermal Characterization of AlGaIn/GaN HEMTs Grown on Silicon. IEEE Transactions on Electron Devices, 2005, 52, 1698-1705.	1.6	78
112	Accelerated Aging of GaN Light Emitting Diodes Studied by 1/f and RTS Noise. AIP Conference Proceedings, 2005, , .	0.3	0
113	Technology, properties and limitations of state-of-the-art InAlN/GaN HEMTs. , 2005, , .		0
114	A new numerical and experimental analysis tool for ESD devices by means of the transient interferometric technique. IEEE Electron Device Letters, 2005, 26, 916-918.	2.2	11
115	ZrO2/(Al)GaN metalâ€oxideâ€semiconductor structures: characterization and application. Semiconductor Science and Technology, 2004, 19, 1364-1368.	1.0	34
116	Electrical overstress in AlGaIn/GaN HEMTs: study of degradation processes. Solid-State Electronics, 2004, 48, 271-276.	0.8	24
117	Material and device issues of AlGaIn/GaN HEMTs on silicon substrates. Microelectronics Journal, 2003, 34, 435-437.	1.1	13
118	Electrostatic discharge effects in AlGaIn/GaN high-electron-mobility transistors. Applied Physics Letters, 2003, 83, 4655-4657.	1.5	43
119	Thermal distribution during destructive pulses in ESD protection devices using a single-shot two-dimensional interferometric method. IEEE Transactions on Device and Materials Reliability, 2003, 3, 197-201.	1.5	11
120	Annealing of Schottky contacts deposited on dry etched AlGaIn/GaN. Semiconductor Science and Technology, 2002, 17, L76-L78.	1.0	19
121	InAlN/(In)GaN high electron mobility transistors: some aspects of the quantum well heterostructure proposal. Semiconductor Science and Technology, 2002, 17, 540-544.	1.0	131
122	Determination of channel temperature in AlGaIn/GaN HEMTs grown on sapphire and silicon substrates using DC characterization method. IEEE Transactions on Electron Devices, 2002, 49, 1496-1498.	1.6	176
123	Electrical field mapping in InGaP HEMTs and GaAs terahertz emitters using backside infrared OBIC technique.. Microelectronics Reliability, 2002, 42, 1673-1677.	0.9	0
124	Power electronics on InAlN/(In)GaN: Prospect for a record performance. IEEE Electron Device Letters, 2001, 22, 510-512.	2.2	516
125	Technology and performance of 150nm gate length InGaP/InGaAs/GaAs pHEMTs. Vacuum, 2001, 61, 323-327.	1.6	4
126	InGaAs/InGaP HEMTs: technological optimization and analytical modelling. Vacuum, 2001, 61, 333-337.	1.6	1



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127	Study of the correlation between GaN material properties and the growth conditions of radio frequency plasma-assisted molecular beam epitaxy. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2001, 80, 304-308.	1.7	8
128	Performance of GaAs micromachined microactuator. <i>Sensors and Actuators A: Physical</i> , 2000, 85, 365-370.	2.0	11
129	Thermal actuation of a GaAs cantilever beam. <i>Journal of Micromechanics and Microengineering</i> , 2000, 10, 293-298.	1.5	23
130	Patterning of cantilevers for power sensor microsystem. <i>Vacuum</i> , 1998, 51, 307-309.	1.6	10
131	Study of thermal effects in GaAs micromachined power sensor microsystems by an optical interferometer technique. <i>Microelectronics Journal</i> , 1998, 29, 191-198.	1.1	6
132	6H-SiC Schottky Diode Edge Terminated Using Amorphous SiC by Sputtering Method. <i>Materials Science Forum</i> , 1998, 264-268, 925-928.	0.3	4
133	Schottky contacts on reactive-ion etched InGaP. <i>Journal of Vacuum Science &amp; Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1997, 15, 2016.	1.6	1
134	Schottky contact investigation on reactive ion etched 6H $\hat{\Gamma}$ -SiC. <i>Diamond and Related Materials</i> , 1997, 6, 1459-1462.	1.8	1
135	The fabrication of thin GaAs cantilever beams for power sensor microsystem using RIE. <i>Vacuum</i> , 1996, 47, 1215-1217.	1.6	16
136	Monolithic GaAs MESFET power sensor microsystem. <i>Electronics Letters</i> , 1995, 31, 1914-1915.	0.5	31
137	Study of Schottky contact formation on CH <sub>4</sub> /H <sub>2</sub> reactive-ion-etched InAlAs. <i>Semiconductor Science and Technology</i> , 1994, 9, 1226-1229.	1.0	4
138	Co-implantation of Mg and Si in GaAs MESFETs. <i>Solid-State Electronics</i> , 1993, 36, 427-430.	0.8	2
139	Reactive ion etching of $\hat{\Gamma}$ -SiC in CCl <sub>2</sub> F <sub>2</sub> /O <sub>2</sub> . <i>Electronics Letters</i> , 1993, 29, 18-19.	0.5	4
140	The PHOTOFET method in submicrometre GaAs MESFETS: substrate leakage current effect. <i>Semiconductor Science and Technology</i> , 1992, 7, 935-939.	1.0	0
141	Properties of WN <sub>x</sub> /GaAs Schottky contacts prepared by ion implantation of nitrogen. <i>Journal of Materials Science: Materials in Electronics</i> , 1992, 3, 157-161.	1.1	3
142	d.c. Performance of short-channel ion-implanted GaAs MESFETs (The role of gate length shortening). <i>Solid-State Electronics</i> , 1990, 33, 1223-1227.	0.8	9
143	A three layer model of planar alloyed ohmic contacts to n-GaAs. <i>Solid-State Electronics</i> , 1990, 33, 1531-1538.	0.8	1
144	Improvements in three-terminal thermoconverter technique. , 0, , .		0

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145	Thin film resistance temperature sensors on GaAs. , 0, , .		0
146	Study of bimetallic effect in a GaAs cantilever beam of power sensor microsystem. , 0, , .		1
147	Investigation of self-heating effects in AlGaIn-GaN HEMTs. , 0, , .		1
148	Thermal distribution during destructive pulses in ESD protection devices using a single-shot, two-dimensional interferometric method. , 0, , .		3
149	Backgating, high-current and breakdown characterisation of AlGaIn/GaN HEMTs on silicon substrates. , 0, , .		2
150	Transient interferometric mapping of temperature and free carriers in semiconductor devices. , 0, , .		0
151	Low frequency noise characterization of the GaN LEDs. , 0, , .		0
152	Predictive device simulation for ESD protection structures validated with transient interferometric thermal-mapping experiments. , 0, , .		1